

Vishay Semiconductors

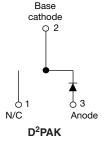
Hyperfast Rectifier, 30 A FRED Pt®

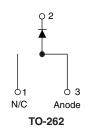


VS-ETH3006S-M3



VS-ETH3006-1-M3

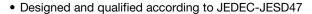




PRODUCT SUMMARY	
Package	TO-263AB (D ² PAK), TO-262AA
I _{F(AV)}	30 A
V _R	600 V
V _F at I _F	2.65 V
t _{rr} (typ.)	27 ns
T _J max.	175 °C
Diode variation	Single die

FEATURES

- Hyperfast recovery time
- · Low forward voltage drop
- 175 °C operating junction temperature
- Low leakage current
- Compliant to RoHS Directive 2002/95/EC
- Halogen-free according to IEC 61249-2-21 definition







ROHS COMPLIANT HALOGEN FREE

DESCRIPTION/APPLICATIONS

Hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC Boost stage in the AC/DC section of SMPS, inverters or as freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS			
Repetitive peak reverse voltage	V _{RRM}		600	V			
Average rectified forward current	I _{F(AV)}	T _C = 95 °C	30				
Non-repetitive peak surge current	I _{FSM}	T _C = 25 °C	180	A			
Operating junction and storage temperatures	T _J , T _{Stg}		- 65 to 175	°C			

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	600	-	-	
Forward voltage	\/_	I _F = 30 A	-	2.0	2.65	V
Forward voltage V _F	VF	$I_F = 30 \text{ A}, T_J = 150 ^{\circ}\text{C}$	-	1.4	1.8	
Poverse leekage ourrent		$V_R = V_R$ rated	-	0.02	30	
Reverse leakage current	I _R	$T_J = 150 ^{\circ}\text{C}, V_R = V_R \text{rated}$	-	50	300	μA
Junction capacitance	C _T	V _R = 600 V	-	20	-	pF
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nH

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Vishay Semiconductors Hyperfast Rectifier, 30 A FRED Pt®



DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS	
		$I_F = 1 \text{ A}, dI_F/dt = 50$	0 A/μs, V _R = 30 V	-	26	35	
Reverse recovery time	t _{rr}	T _J = 25 °C	$I_F = 30 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 200 \text{ V}$	-	26	-	ns
		T _J = 125 °C		-	70	-	
Dook receivery ourrent	,	T _J = 25 °C		-	3.5	-	Α
Peak recovery current	IRRM	T _J = 125 °C		-	7.6	-	^
Reverse recovery charge		T _J = 25 °C		-	50	-	nC
	Q _{rr}	T _J = 125 °C		-	280	-	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range	T _J , T _{Stg}		- 65	-	175	°C	
Thermal resistance, junction to case	R _{thJC}		-	0.95	1.4	°C/W	
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	70		
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.5	-		
Maiabt			-	2.0	-	g	
Weight			-	0.07	-	OZ.	
Mounting torque			6 (5)	-	12 (10)	kgf · cm (lbf · in)	
Marking device		Case style D ² PAK modified	ETH3006S				
Marking device		Case style TO-262		ETH3006-1			



Hyperfast Rectifier, 30 A FRED Pt® Vishay Semiconductors

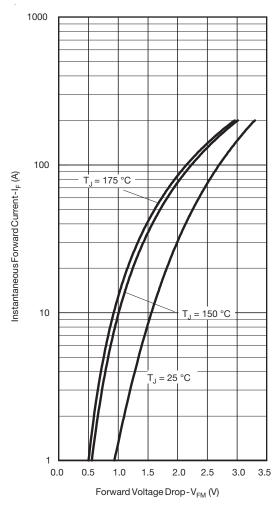


Fig. 1 - Typical Forward Voltage Drop Characteristics

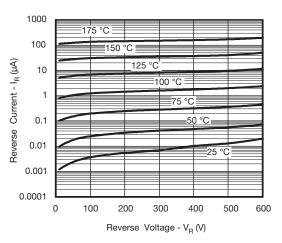


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

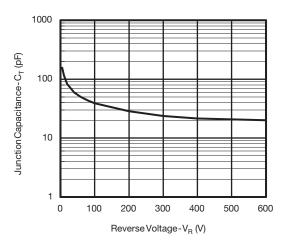


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

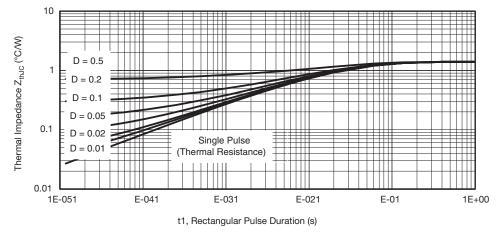


Fig. 4 - Max. Thermal Impedance Z_{thJC} Characteristics

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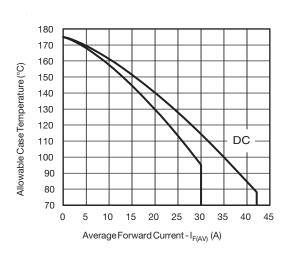


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

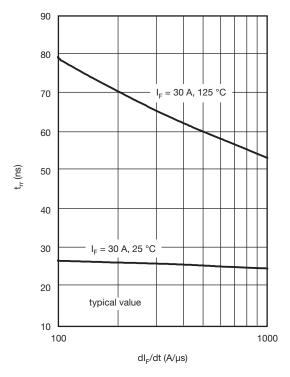


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

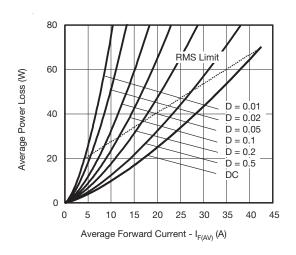


Fig. 6 - Forward Power Loss Characteristics

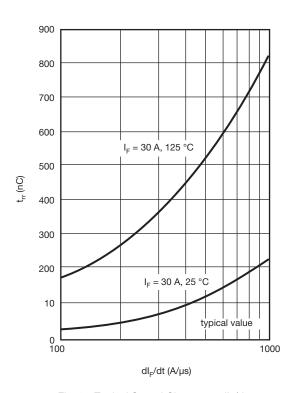


Fig. 8 - Typical Stored Charge vs. dl_F/dt



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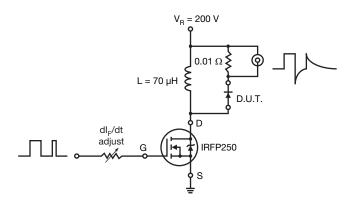
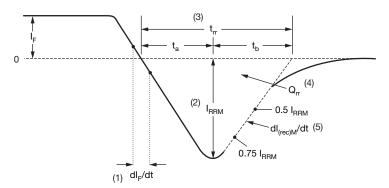


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) Q_{rr} area under curve defined by t_{rr} and I_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $dI_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

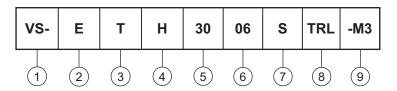
Fig. 10 - Reverse Recovery Waveform and Definitions

Vishay Semiconductors Hyperfast Rectifier, 30 A FRED Pt®



ORDERING INFORMATION TABLE

Device code



Vishay Semiconductors product

Circuit configuration

E = Single diode

T = TO-220

H = Hyperfast recovery time

Current code (30 = 30 A)

Voltage code (06 = 600 V)

• $S = D^2PAK$

• -1 = TO-262

8 • None = Tube (50 pieces)

• TRL = Tape and reel (left oriented, for D2PAK package)

• TRR = Tape and reel (right oriented, for D²PAK package)

-M3 = Halogen-free, RoHS compliant, and terminations lead (Pb)-free 9

ORDERING INFORMATION (Example)						
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION			
VS-ETH3006S-M3	50	1000	Antistatic plastic tube			
VS-ETH3006-1-M3	50	1000	Antistatic plastic tube			
VS-ETH3006STRR-M3	800	800	13" diameter reel			
VS-ETH3006STRL-M3	800	800	13" diameter reel			

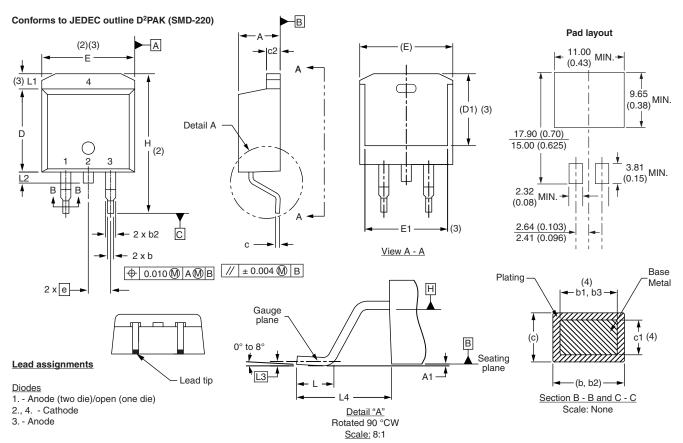
LINKS TO RELATED DOCUMENTS					
Dimensions	TO-263AB (D ² PAK)	www.vishay.com/doc?95046			
Dimensions	TO-262AA	www.vishay.com/doc?95419			
Part marking information	TO-263AB (D ² PAK)	www.vishay.com/doc?95444			
Part marking information	TO-262AA	www.vishay.com/doc?95443			
Packaging information	TO-263AB (D ² PAK)	www.vishay.com/doc?95032			



Vishay Semiconductors

D²PAK

DIMENSIONS in millimeters and inches



SYMBOL	MILLIMETERS		INC	HES	NOTES
STWIDOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.06	4.83	0.160	0.190	
A1	0.00	0.254	0.000	0.010	
b	0.51	0.99	0.020	0.039	
b1	0.51	0.89	0.020	0.035	4
b2	1.14	1.78	0.045	0.070	
b3	1.14	1.73	0.045	0.068	4
С	0.38	0.74	0.015	0.029	
c1	0.38	0.58	0.015	0.023	4
c2	1.14	1.65	0.045	0.065	
D	8.51	9.65	0.335	0.380	2

SYMBOL	MILLIMETERS INCHES		NOTES			
STIMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	
D1	6.86	8.00	0.270	0.315	3	
Е	9.65	10.67	0.380	0.420	2, 3	
E1	7.90	8.80	0.311	0.346	3	
е	2.54 BSC		0.100 BSC			
Н	14.61	15.88	0.575	0.625		
L	1.78	2.79	0.070	0.110		
L1	-	1.65	-	0.066	3	
L2	1.27	1.78	0.050	0.070		
L3	0.25	BSC	0.010	BSC		
L4	4.78	5.28	0.188	0.208		

Notes

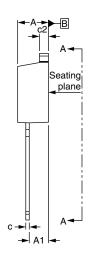
- $^{(1)}$ Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inch
- (7) Outline conforms to JEDEC outline TO-263AB

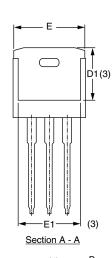


Vishay Semiconductors

TO-262

DIMENSIONS in millimeters and inches



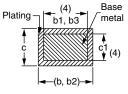


⊕ 0.010**⋒**|A**⋒**|B

Lead assignments



<u>Diodes</u>
1. - Anode (two die)/open (one die)
2., 4. - Cathode
3. - Anode



Section B - B and C - C Scale: None

CYMPOL	MILLIN	METERS	INC	INCHES	
SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.06	4.83	0.160	0.190	
A1	2.03	3.02	0.080	0.119	
b	0.51	0.99	0.020	0.039	
b1	0.51	0.89	0.020	0.035	4
b2	1.14	1.78	0.045	0.070	
b3	1.14	1.73	0.045	0.068	4
С	0.38	0.74	0.015	0.029	
c1	0.38	0.58	0.015	0.023	4
c2	1.14	1.65	0.045	0.065	
D	8.51	9.65	0.335	0.380	2
D1	6.86	8.00	0.270	0.315	3
Е	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
е	2.54	BSC	0.100	BSC	
L	13.46	14.10	0.530	0.555	
L1	=	1.65	-	0.065	3
L2	3.56	3.71	0.140	0.146	

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- $^{(3)}$ Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Controlling dimension: inches
- (6) Outline conform to JEDEC TO-262 except A1 (maximum), b (minimum) and D1 (minimum) where dimensions derived the actual package outline





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